

BDX54/A/B/C

Hammer Drivers, Audio Amplifiers Applications Power Liner and Switching Applications

- Power Darlington TR
- Complement to BDX53, BDX53A, BDX53B and BDX53C respectively



1.Base 2.Collector 3.Emitter

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter		Value	Units
V _{CBO}	Collector-Base Voltage : BDX54	4 10	- 45	V
	: BDX54A	~ 为事	- 60	V
	: BDX54B	1 19	- 80	V
	: BDX54C	40 13	- 100	V
V _{CEO}	Collector-Emitter Voltage : BDX54	135	- 45	V
	: BDX54A		- 60	V
	: BDX54B		- 80	V
	: BDX54C		- 100	V
V _{EBO}	Emitter-Base Voltage		- 5	V
I _C	Collector Current (DC)		- 8	Α
I _{CP}	*Collector Current (Pulse)		- 12	А
I _B	Base Current		- 0.2	Α
P _C	Collector Dissipation (T _C =25°C)		60	W
T _J	Junction Temperature		150	°C
T _{STG}	Storage Temperature		- 65 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V _{CEO} (sus)	* Collector-Emitter Sustaining Voltage					
	: BDX54	$I_C = -100 \text{mA}, I_B = 0$	- 45			V
	: BDX54A		- 60			V
	: BDX54B		- 80			V
	: BDX54C		- 100			V
I _{CBO}	Collector Cut-off Current : BDX54	$V_{CB} = -45V, I_{E} = 0$			- 200	μΑ
	: BDX54A	$V_{CB} = -60V, I_{E} = 0$			- 200	μΑ
	: BDX54B	$V_{CB} = -80V, I_{E} = 0$			- 200	μΑ
	: BDX54C	$V_{CB} = -100V, I_{E} = 0$			- 200	μΑ
I _{CEO}	Collector Cut-off Current : BDX54	$V_{CE} = -22V, I_{B} = 0$			- 500	μΑ
	: BDX54A	$V_{CE} = -30V, I_{B} = 0$			- 500	μΑ
	: BDX54B	$V_{CE} = -40V, I_{B} = 0$			- 500	μΑ
	: BDX54C	$V_{CE} = -50V, I_{B} = 0$			- 500	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$			- 2	mA
h _{FE}	* DC Current Gain	$V_{CE} = -3V, I_{C} = -3A$	750			
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	$I_C = -3A, I_B = -12mA$			- 2	V
V _{BE} (sat)	* Base-Emitter Saturation Voltage	$I_C = -3A, I_B = -12mA$			- 2.5	V
V _F	* Parallel Diode Forward Voltage	I _F = - 3A		- 1.8	- 2.5	V
		I _F = - 8A		- 2.5		V

©2000 Fairchild Semiconductor International Rev. A, February 2000

Typical Characteristics V_{CE} = -3V I_C = 250I_B V_{BE}(sat)[V], SATURATION VOLTAGE -3.0 hFE, DC CURRENT GAIN -2.8 -2.6 -2.2 -2.0 -1.4 -10 I_c[A], COLLECTOR CURRENT I_c[A], COLLECTOR CURRENT Figure 2. Base-Emitter Saturation Voltage Figure 1. DC current Gain I_C = 250I_B V_{cE}(sat)[V], SATURATION VOLTAGE V_F(sat)[V], FORWARD VOLTAGE -2.4 -2.2 -2.0 -1.6 -1.8 -1.6 -1.4 -1.2 -1.0 I_F[A], FORWARD CURRENT I_c[A], COLLECTOR CURRENT Figure 3. Collector-Emitter Saturation Voltage Figure 4. Damper Diode Forward Voltage Ic[A], COLLECTOR CURRENT P_D[W], POWER DISSIPATION BDX54A BDX54B BDX54C $V_{CE}[V]$, COLLECTOR-EMITTER VOLTAGE T_C[°C], CASE TEMPERATURE Figure 5. Safe Operating Area Figure 6. Power Derating

©2000 Fairchild Semiconductor International Rev. A, February 2000

Package Demensions TO-220 9.90 ±0.20 4.50 ± 0.20 (8.70) $2.80 \pm\! 0.10$ 1.30 +0.10 -0.05 Ø3.60 ±0.10 (3.70) 9.20 ±0.20 (1.46) 13.08 ±0.20 10.08 ±0.30 0.80 ±0.10 0.50 +0.10 -0.05 2.40 ±0.20 2.54TYP 2.54TYP [2.54 ±0.20] [2.54 ±0.20] 10.00 ±0.20 Dimensions in Millimeters

©2000 Fairchild Semiconductor International Rev. A, February 2000

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

 $\begin{array}{ll} \mathsf{FACT^{\mathsf{TM}}} & \mathsf{QFET^{\mathsf{TM}}} \\ \mathsf{FACT} \ \mathsf{Quiet} \ \mathsf{Series^{\mathsf{TM}}} & \mathsf{QS^{\mathsf{TM}}} \end{array}$

FAST[®] Quiet Series[™]
FASTr[™] SuperSOT[™]-3
GTO[™] SuperSOT[™]-6

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR INTERNATIONAL.

As used herein:

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

©2000 Fairchild Semiconductor International Rev. E